WHAT IS CLAIMED IS:

1. A method of manufacturing a semiconductor device, comprising:

mounting a semiconductor chip having electrodes on a substrate having wiring patterns; and

forming conductive layers that electrically connect the electrodes and the wiring patterns in a manner to pass side surfaces of the semiconductor chip.

2. The method of manufacturing a semiconductor device according to claim 1, further including face-up bonding the semiconductor chip.

3. A method of manufacturing a semiconductor device, comprising:

stacking in layers a plurality of semiconductor chips having electrodes on a substrate having wiring patterns; and

forming a conductive layer that electrically connects the electrodes of any one of the semiconductor chips and the wiring patterns in a manner to pass a side surface of at least one of the semiconductor chips.

4. The method of manufacturing a semiconductor device according to claim 3, further including face-up bonding the plurality of semiconductor chips.

5. The method of manufacturing a semiconductor device according to claim 3, further including mounting a second semiconductor chip, that is smaller than a first semiconductor chip among the plurality of semiconductor chips, on the first semiconductor chip.

6. The method of manufacturing a semiconductor device according to claim 3, further including forming a second conductive layer that electrically connects the electrodes of one of the semiconductor chips and the electrodes of another of the semiconductor chips in a manner to pass a side surface of at least one of the semiconductor chips.

7. The method of manufacturing a semiconductor device according to claim 3, further including face-down bonding a first semiconductor chip among the plurality of semiconductor chips to the substrate, and face-up bonding a second semiconductor chip to a side of the first semiconductor chip opposite to a side where the electrodes are formed.

8. The method of manufacturing a semiconductor device according to claim 1, further including forming the conductive layer by ejecting a solution containing fine-particles of conductive material.

9. A semiconductor device, comprising:

a substrate having wiring patterns;

a plurality of stacked semiconductor chips having electrodes;

a conductive layer that electrically connects the electrodes of any one of the semiconductor chips and the wiring patterns in a manner to pass a side surface of at least one of the semiconductor chips; and

a second conductive layer that electrically connects the electrodes of one of the semiconductor chips and the electrodes of another of the semiconductor chips in a manner to pass a side surface of at least one of the semiconductor chips.

10. The semiconductor device according to claim 9, the plurality of semiconductor chips being face-up bonded.

11. The semiconductor device according to claim 10, a second semiconductor chip that is smaller than a first semiconductor chip among the plurality of semiconductor chips being mounted on the first semiconductor chip.

12. The semiconductor device according to claim 9, a first semiconductor chip among the plurality of semiconductor chips being face-down bonded to the substrate, and a second semiconductor chip being face-up bonded to a side of the first semiconductor chip opposite to a side thereof where the electrodes are formed.

13. A circuit substrate assembly, comprising:

a circuit substrate; and

the semiconductor device according to claim 9 mounted on the circuit substrate.

14. An electronic equipment, comprising:

the semiconductor device according to claim 9.